

## PCI-EXPRESS GEN 2 SINGLE OUTPUT CLOCK GENERATOR

### Features

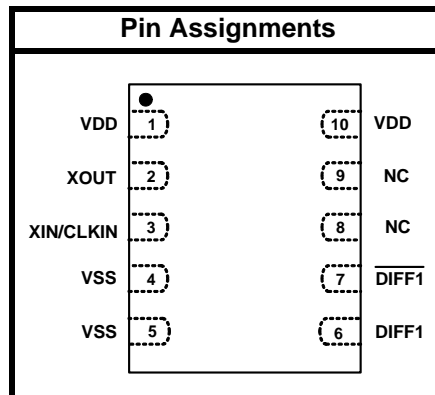
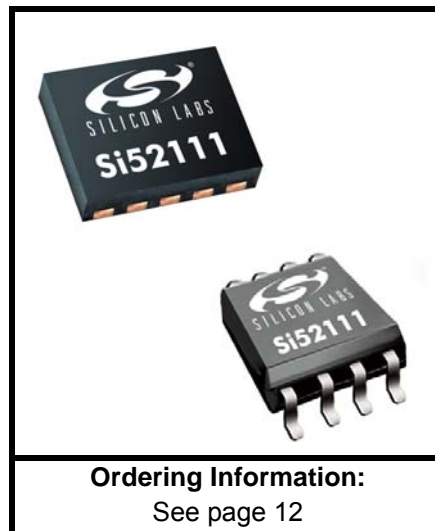
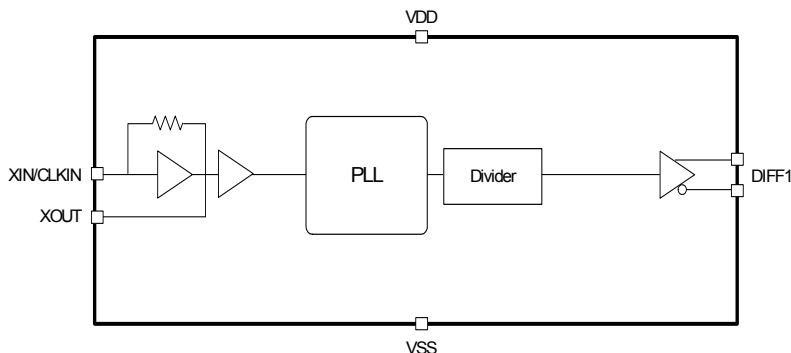
- PCI-Express Gen 1 and Gen 2 compliant
- Low power HCSL differential output buffer
- Supports Serial-ATA (SATA) at 100 MHz
- No termination resistors required
- 25 MHz Crystal Input or Clock input
- Triangular spread spectrum profile for maximum EMI reduction (Si52111-B4)
- Extended Temperature: -40 to 85 °C
- 3.3 V Power supply
- Small package 10-pin TDFN (3x3 mm)
- Si52111-B3 does not support spread spectrum outputs
- Si52111-B4 supports 0.5% down spread outputs
- For PCIe Gen 3 applications, see Si52111-B5/B6

### Applications

- Network Attached Storage
- Multi-function Printer
- Wireless Access Point
- Routers

### Description

Si52111-B3/B4 is a high-performance, PCIe clock generator that can source one PCIe clock output from a 25 MHz crystal or clock input. The clock output is compliant to PCIe Gen 1 and Gen 2 specifications. The ultra-small footprint (3x3 mm) and industry leading low power consumption make Si52111-B3/B4 the ideal clock solution for consumer and embedded applications.



Patents pending



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# Si52111-B3/B4

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## 1. Electrical Specifications

**Table 1. Recommended Operating Conditions**

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Supply Voltage (extended)	$V_{DD(\text{extended})}$	3.3 V $\pm$ 5%	3.13	3.3	3.46	V
Supply Voltage (commercial)	$V_{DD(\text{commercial})}$	3.3 V $\pm$ 10%	2.97	3.3	3.63	V

**Table 2. DC Electrical Specifications**

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Operating Voltage	$V_{DD}$	3.3 V $\pm$ 10%	2.97	3.30	3.63	V
Operating Supply Current	$I_{DD}$	Full Active	—	—	13	mA
Input Pin Capacitance	$C_{IN}$	Input Pin Capacitance	—	3	5	pF
Output Pin Capacitance	$C_{OUT}$	Output Pin Capacitance	—	—	5	pF

Table 3. AC Electrical Specifications

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
<b>Crystal</b>						
Long-term Accuracy	$L_{ACC}$	Measured at $V_{DD}/2$ differential	—	—	250	ppm
<b>Clock Input</b>						
CLKIN Duty Cycle	$T_{DC}$	Measured at $V_{DD}/2$	45	—	55	%
CLKIN Rise and Fall Times	$T_R/T_F$	Measured between $0.2 V_{DD}$ and $0.8 V_{DD}$	0.5	—	4.0	V/ns
CLKIN Cycle-to-Cycle Jitter	$T_{CCJ}$	Measured at $V_{DD}/2$	—	—	250	ps
CLKIN Long Term Jitter	$T_{LTJ}$	Measured at $V_{DD}/2$	—	—	350	ps
Input High Voltage	$V_{IH}$	XIN/CLKIN pin	2	—	$V_{DD}+0.3$	V
Input Low Voltage	$V_{IL}$	XIN/CLKIN pin	—	—	0.8	V
Input High Current	$I_{IH}$	XIN/CLKIN pin, $V_{IN} = V_{DD}$	—	—	35	uA
Input Low Current	$I_{IL}$	XIN/CLKIN pin, $0 < V_{IN} < 0.8$	-35	—	—	uA
<b>DIFF Clocks</b>						
Duty Cycle	$T_{DC}$	Measured at 0 V differential	45	—	55	%
Skew	$T_{SKEW}$	Measured at 0 V differential	—	—	60	ps
Output Frequency	$F_{OUT}$	$V_{DD} = 3.3 V$	—	100	—	MHz
Frequency Accuracy	$F_{ACC}$	All output clocks	—	—	100	ppm
Slew Rate	$t_{r/f2}$	Measured differentially from $\pm 150 mV$	0.6	—	4.0	V/ns
Cycle-to-Cycle Jitter	$T_{CCJ}$	Measured at 0 V differential	—	28	70	ps
PCIe Gen 1 Pk-Pk Jitter	$PK-PK_{GEN1}$	PCIe Gen 1	—	24	86	ps
PCIe Gen 2 Phase Jitter	$RMS_{GEN2}$	$10 kHz < F < 1.5 MHz$	—	1.35	3.0	ps
		$1.5 MHz < F < Nyquist$	—	1.4	3.1	ps
Crossing Point Voltage at 0.7 V Swing	$V_{OX}$		300	—	550	mV
Voltage High	$V_{HIGH}$		—	—	1.15	V
Voltage Low	$V_{LOW}$		-0.3	—	—	V
Spread Range	$S_{RNG}$	Down Spread, -B4 only	—	-0.5	—	%
Modulation Frequency	$F_{MOD}$	-B4 only	30	31.5	33	kHz
<b>Enable/Disable and Set-up</b>						
Clock Stabilization from Power-up	$T_{STABLE}$		—	—	3	ms
Stopclock Set-up Time	$T_{SS}$		10.0	—	—	ns
<b>Note:</b> Visit <a href="http://www.pcsig.com">www.pcsig.com</a> for complete PCIe specifications.						

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**Table 4. Thermal Conditions**

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Temperature, Storage	$T_S$	Non-functional	-65	—	150	°C
Temperature, Operating Ambient	$T_A$	Functional	-40	—	85	°C
Temperature, Junction	$T_J$	Functional	—	—	150	°C
Dissipation, Junction to Case (TDFN)	$\theta_{JC}$	JEDEC (JESD 51)	—	—	38.3	°C/W
Dissipation, Junction to Case (TSSOP)	$\theta_{JC}$	JEDEC (JESD 51)	—	—	37.0	°C/W
Dissipation, Junction to Ambient (TDFN)	$\theta_{JA}$	JEDEC (JESD 51)	—	—	90.4	°C/W
Dissipation, Junction to Ambient (TSSOP)	$\theta_{JA}$	JEDEC (JESD 51)	—	—	124.0	°C/W

**Table 5. Absolute Maximum Conditions**

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Main Supply Voltage	$V_{DD\_3.3V}$		—		4.6	V
Input Voltage	$V_{IN}$	Relative to $V_{SS}$	-0.5		4.6	$V_{DC}$
ESD Protection (Human Body Model)	$ESD_{HBM}$	JEDEC (JESD 22 - A114)	2000		—	V
Flammability Rating	UL-94	UL (Class)	V-0			

**Note:** While using multiple power supplies, the voltage on any input or I/O pin cannot exceed the power pin during power-up. Power supply sequencing is not required..

## 2. Crystal Recommendations

If using a crystal input, the device requires a parallel resonance crystal.

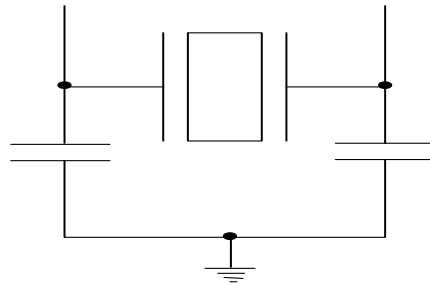
**Table 6. Crystal Recommendations**

Frequency (Fund)	Cut	Loading	Load Cap	ESR	Drive	Shunt Cap (max)	Motional (max)	Tolerance (max)	Stability (max)	Aging (max)
25 MHz	AT	Parallel	12–15 pF	<50 $\Omega$	>150 $\mu$ W	5 pF	0.016 pF	35 ppm	30 ppm	5 ppm

### 2.1. Crystal Loading

Crystal loading is critical in achieving low ppm performance. To realize low ppm performance, use the total capacitance the crystal sees to calculate the appropriate capacitive loading (CL).

Figure 1 shows a typical crystal configuration using two trim capacitors. It is important that the trim capacitors are in series with the crystal.



**Figure 1. Crystal Capacitive Clarification**

## 2.2. Calculating Load Capacitors

In addition to the standard external trim capacitors, consider the trace capacitance and pin capacitance to calculate the crystal loading correctly. Again, the capacitance on each side is in series with the crystal. The total capacitance on both sides is twice the specified crystal load capacitance (CL). Trim capacitors are calculated to provide equal capacitive loading on both sides.



**Figure 2. Crystal Loading Example**

Use the following formulas to calculate the trim capacitor values for Ce1 and Ce2.

### Load Capacitance (each side)

$$C_e = 2 \times CL - (C_s + C_i)$$

### Total Capacitance (as seen by the crystal)

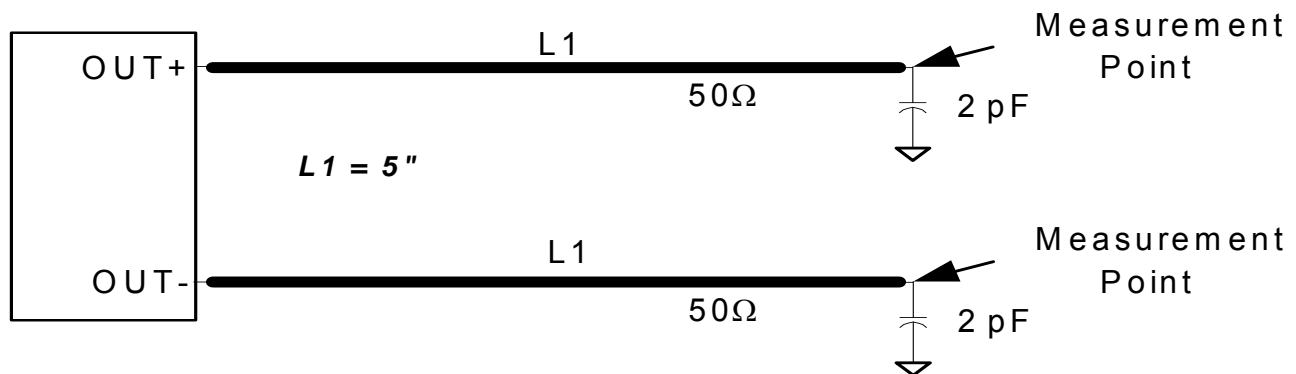
$$CL_e = \frac{1}{\left( \frac{1}{C_{e1} + C_{s1} + C_{i1}} + \frac{1}{C_{e2} + C_{s2} + C_{i2}} \right)}$$

- CL: Crystal load capacitance
- CL<sub>e</sub>: Actual loading seen by crystal using standard value trim capacitors
- C<sub>e</sub>: External trim capacitors
- C<sub>s</sub>: Stray capacitance (terraced)
- C<sub>i</sub>: Internal capacitance (lead frame, bond wires, etc.)

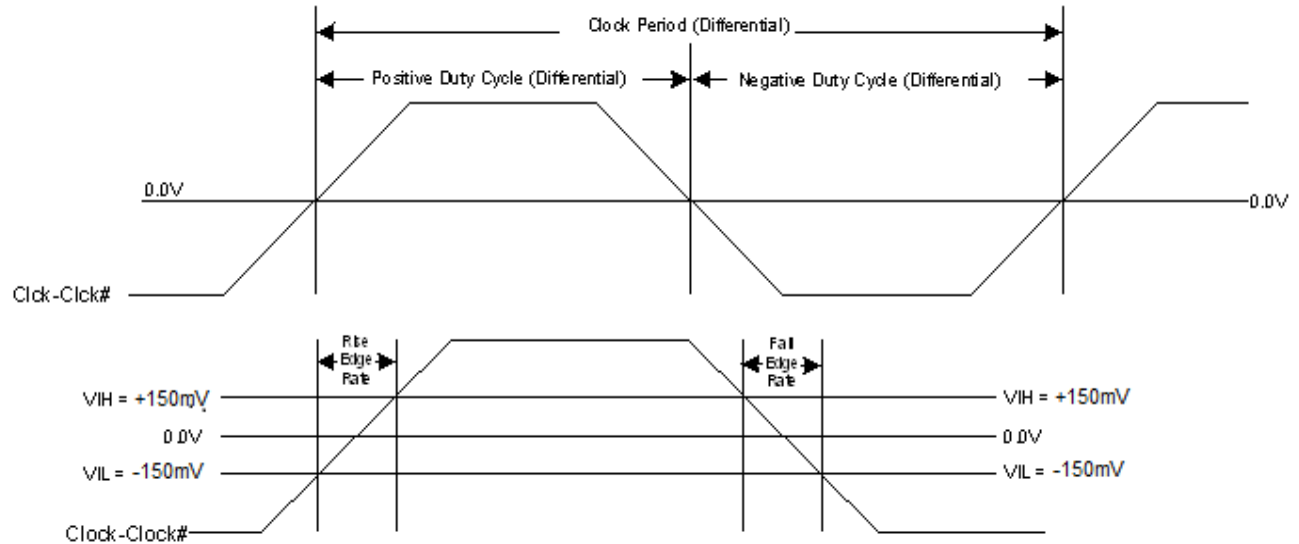


### 3. Test and Measurement Setup

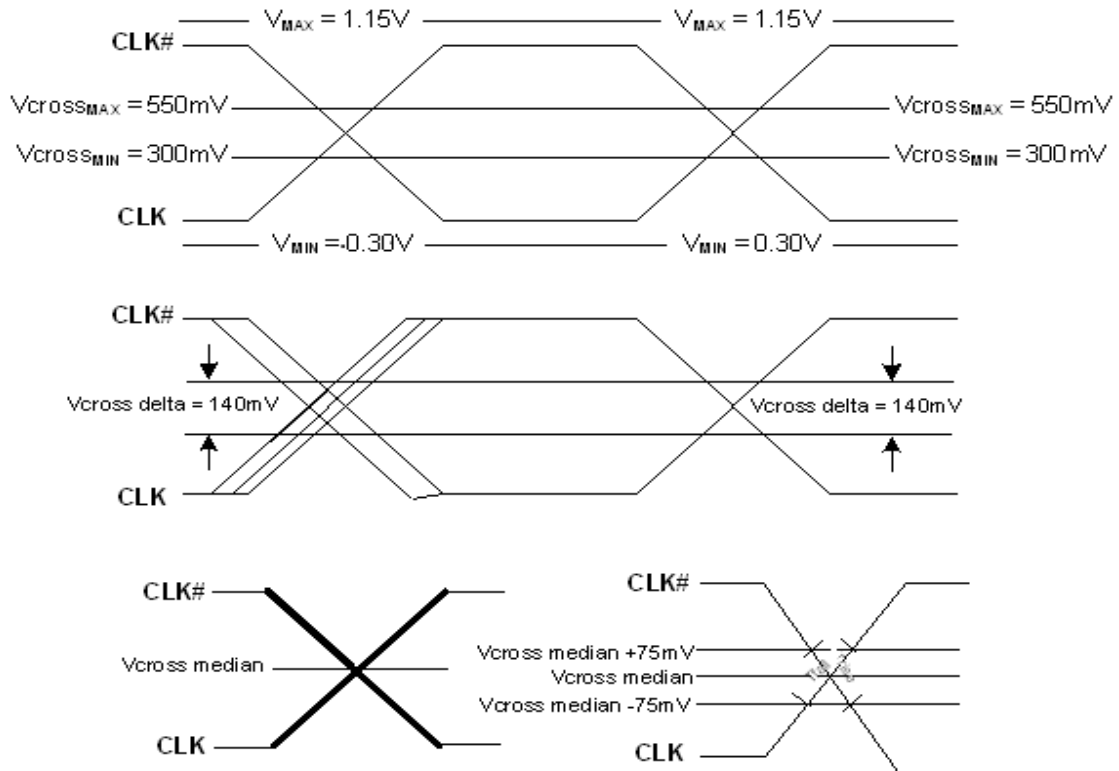
Figures 3 through 5 show the test load configuration for the differential clock signals.



**Figure 3. 0.7 V Differential Load Configuration**



**Figure 4. Differential Measurement for Differential Output Signals (for AC Parameters Measurement)**



**Figure 5. Single-Ended Measurement for Differential Output Signals (for AC Parameters Measurement)**

## 4. Pin Descriptions

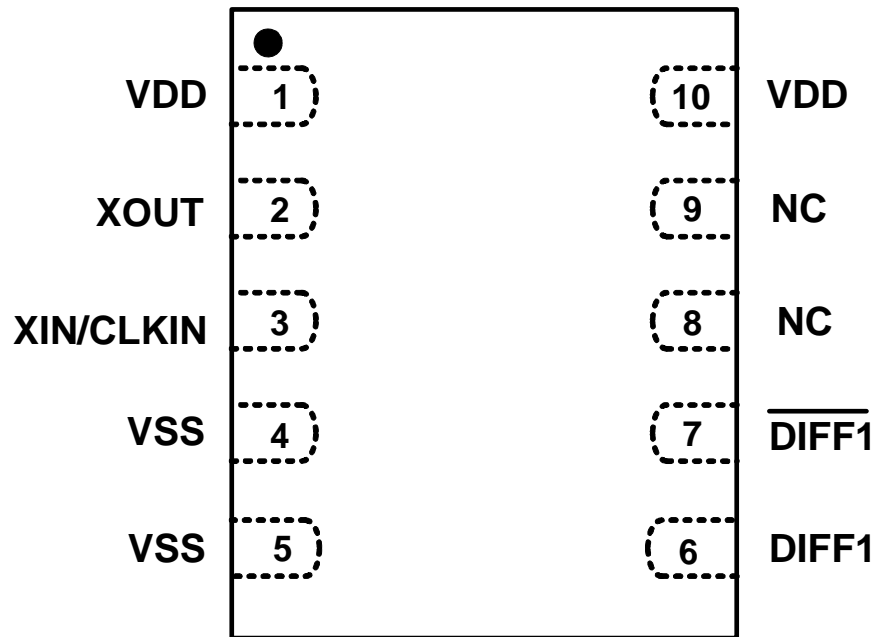


Figure 6. 10-Pin TDFN

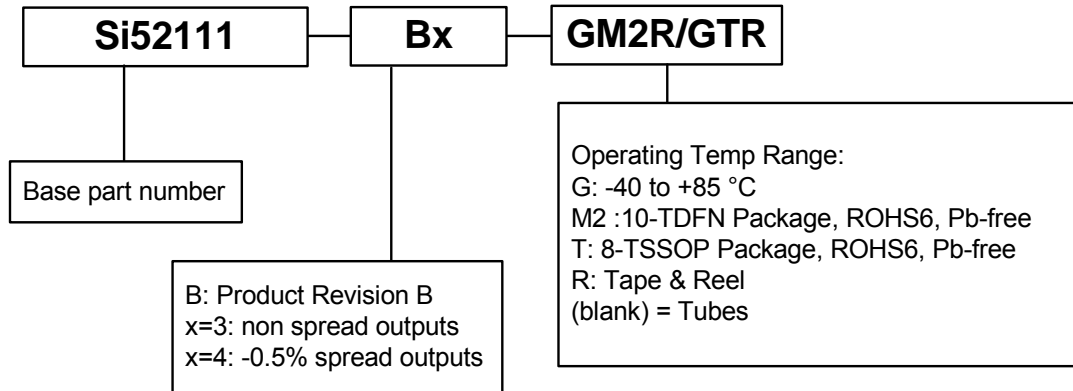
Table 7. 10-Pin TDFN Descriptions

Pin #	Name	Type	Description
1	VDD	PWR	3.3 V Power supply.
2	XOUT	O	25.00 MHz crystal output, Float XOUT if using only CLKIN (clock input).
3	XIN/CLKIN	I	25.00 MHz crystal input or 3.3 V, 25 MHz clock Input.
4	VSS	GND	Ground.
5	VSS	GND	Ground.
6	DIFF1	O, DIF	0.7 V, 100 MHz differentials clock output.
7	$\overline{\text{DIFF1}}$	O, DIF	0.7 V, 100 MHz differentials clock output.
8	NC	NC	No Connect. Do not connect this pin to anything.
9	NC	NC	No Connect. Do not connect this pin to anything.
10	VDD	PWR	3.3 V Power supply

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## 5. Ordering Guide

Part Number	Spread Option	Package Type	Temperature
Si52111-B3-GM2	No Spread	10-pin TDFN	Extended, -40 to 85 °C
Si52111-B3-GM2R	No Spread	10-pin TDFN—Tape and Reel	Extended, -40 to 85 °C
Si52111-B3-GT	No Spread	8-pin TSSOP	Extended, -40 to 85 °C
Si52111-B3-GTR	No Spread	8-pin TSSOP - Tape and Reel	Extended, -40 to 85 °C
Si52111-B4-GM2	-0.5% Spread	10-pin TDFN	Extended, -40 to 85 °C
Si52111-B4-GM2R	-0.5% Spread	10-pin TDFN—Tape and Reel	Extended, -40 to 85 °C
Si52111-B4-GT	-0.5% Spread	8-pin TSSOP	Extended, -40 to 85 °C
Si52111-B4-GTR	-0.5% Spread	8-pin TSSOP - Tape and Reel	Extended, -40 to 85 °C



**Figure 7. Ordering Information**

## 6. Package Outlines

### 6.1. TDFN Package

Figure 8 illustrates the package details for the 10-pin TDFN. Table 8 lists the values for the dimensions shown in the illustration.

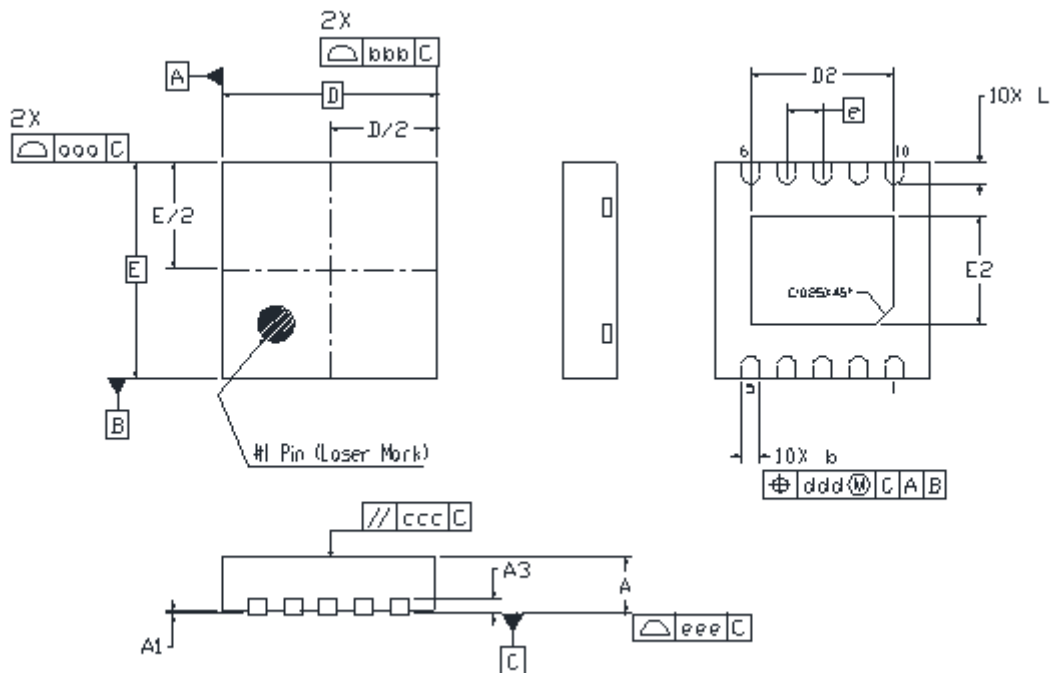


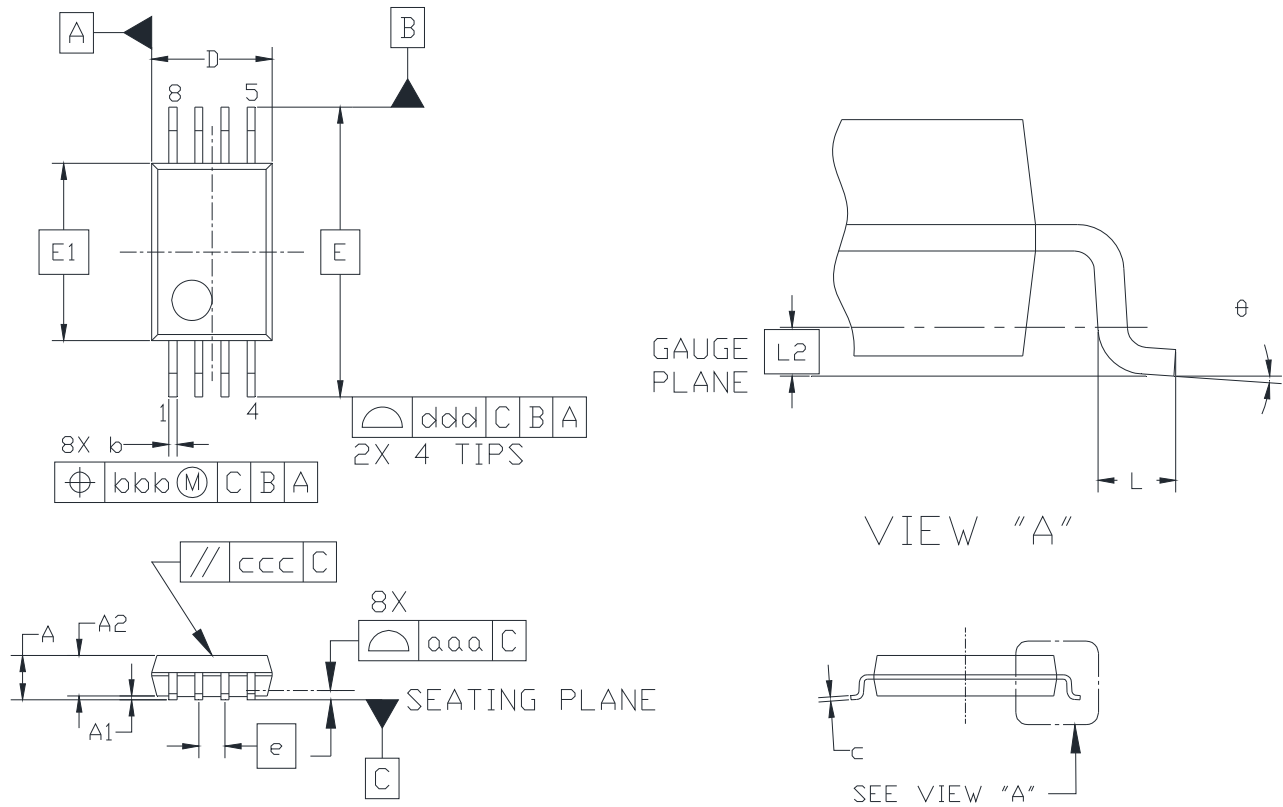
Figure 8. 10-Pin TDFN Package Drawing

**Table 8. TDFN Package Diagram Dimensions**

<b>Symbol</b>	<b>Min</b>	<b>Nom</b>	<b>Max</b>
A	0.70	0.75	0.80
A1	0.00	0.02	0.05
A3	0.20 REF.		
b	0.18	0.25	0.30
D	3.00 BSC.		
D2	1.90	2.00	2.10
e	0.50 BSC		
E	3.00 BSC		
E2	1.40	1.50	1.60
L	0.25	0.30	0.35
aaa	0.10		
bbb	0.10		
ccc	0.10		
ddd	0.10		
eee	0.08		
<b>Notes:</b> <ol style="list-style-type: none"><li>1. All dimensions shown are in millimeters (mm) unless otherwise noted.</li><li>2. Dimensioning and Tolerancing per ANSI Y14.5M-1994.</li><li>3. Recommended card reflow profile is per the JEDEC/IPC J-STD-020 specification for Small Body Components.</li><li>4. This drawing conforms to the JEDEC Solid State Outline MO-229.</li></ol>			

## 7. TSSOP Package

Figure 9 illustrates the package details for the 8-pin TSSOP. Table 9 lists the values for the dimensions shown in the illustration.



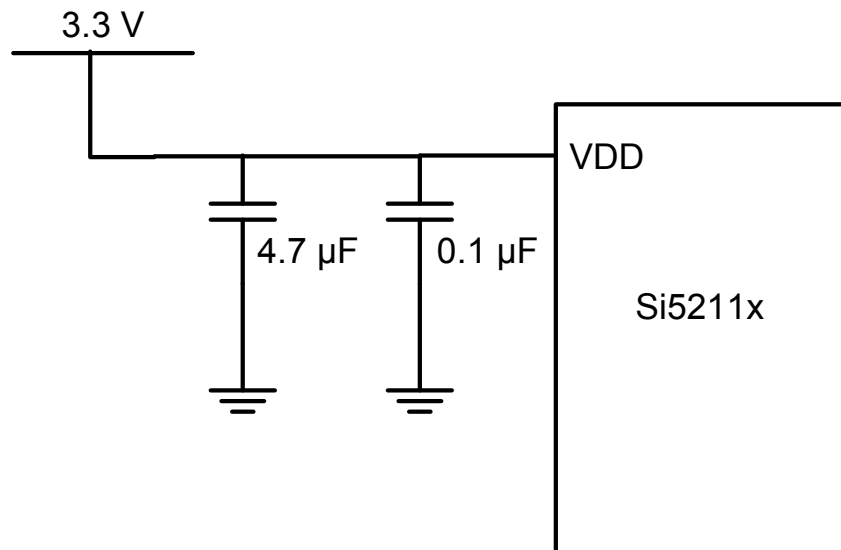
**Figure 9. 8-Pin TSSOP Package Drawing**

**Table 9. TSSOP Package Diagram Dimensions**

Symbol	Min	Nom	Max
A	—	—	1.20
A1	0.05	—	0.15
A2	0.80	0.90	1.05
b	0.19	—	0.30
c	0.09	—	0.20
D	2.90	3.00	3.10
E	6.40 BSC		
E1	4.30	4.40	4.50
e	0.65 BSC		
L	0.45	0.60	0.75
L2	0.25 BSC		
$\theta$	0°	—	8°
aaa	0.10		
bbb	0.10		
ccc	0.05		
ddd	0.20		
<b>Notes:</b>			
<ol style="list-style-type: none"> <li>1. All dimensions shown are in millimeters (mm) unless otherwise noted.</li> <li>2. Dimensioning and Tolerancing per ANSI Y14.5M-1994.</li> <li>3. This drawing conforms to the JEDEC Solid State Outline MO-153, Variation AA.</li> <li>4. Recommended card reflow profile is per the JEDEC/IPC J-STD-020C specification for Small Body Components.</li> </ol>			



## 8. Recommended Design Guideline



**Note:** FB Specifications:  
DC resistance 0.1–0.3  $\Omega$   
Impedance at 100 MHz  $\geq 1000 \Omega$

**Figure 10. Recommended Application Schematic**

## CONTACT INFORMATION

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